

MUR180E, MUR1100E

SWITCHMODE Power Rectifiers

Ultrafast "E" Series with High Reverse Energy Capability

These state-of-the-art devices are designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- 10 mJoules Avalanche Energy Guaranteed
- Excellent Protection Against Voltage Transients in Switching Inductive Load Circuits
- Ultrafast 75 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- Reverse Voltage to 1000 V
- These are Pb-Free Devices*

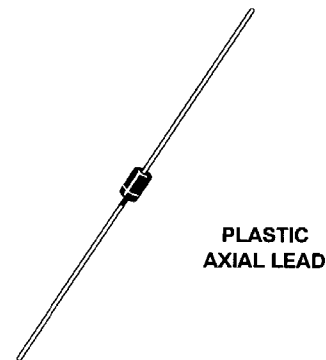
Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped in Plastic Bags; 1,000 per Bag
- Available Tape and Reel; 5,000 per Reel, by Adding a "RL" Suffix to the Part Number
- Polarity: Cathode Indicated by Polarity Band

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	800 1000	V
Average Rectified Forward Current (Note 1) (Square Wave Mounting Method #3 Per Note 3)	$I_{F(AV)}$	1.0 @ $T_A = 95^\circ\text{C}$	A
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}	35	A
Operating Junction Temperature and Storage Temperature Range	T_J, T_{stg}	-65 to +175	°C

ULTRAFAST RECTIFIERS 1.0 AMPERES, 800-1000 VOLTS



PLASTIC
 AXIAL LEAD

MARKING DIAGRAM



- A = Assembly Location
- MUR1x0E = Device Code
x 8 or 10
- Y = Year
- WW = Work Week



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

MUR180E, MUR1100E

THERMAL CHARACTERISTICS

Characteristics	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	See Note 3	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 1.0 \text{ A}$, $T_J = 150^{\circ}\text{C}$) ($I_F = 1.0 \text{ A}$, $T_J = 25^{\circ}\text{C}$)	V_F	1.50 1.75	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 100^{\circ}\text{C}$) (Rated dc Voltage, $T_J = 25^{\circ}\text{C}$)	I_R	600 10	μA
Maximum Reverse Recovery Time ($I_F = 1.0 \text{ A}$, $di/dt = 50 \text{ Amp}/\mu\text{s}$) ($I_F = 0.5 \text{ A}$, $I_R = 1.0 \text{ Amp}$, $I_{REC} = 0.25 \text{ A}$)	t_{rr}	100 75	ns
Maximum Forward Recovery Time ($I_F = 1.0 \text{ A}$, $di/dt = 100 \text{ Amp}/\mu\text{s}$, Recovery to 1.0 V)	t_{fr}	75	ns
Controlled Avalanche Energy (See Test Circuit in Figure 6)	W_{AVAL}	10	mJ
Typical Peak Reverse Recovery Current ($I_F = 1.0 \text{ A}$, $di/dt = 50 \text{ A}/\mu\text{s}$)	I_{RM}	1.7	A

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.